Improved Lyman Ultraviolet Astronomy Capabilities through Enhanced Coatings

By

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Collaborating Institutions:

- Goddard Space Flight Center (GSFC)
- University of Maryland (UMD)
- Naval Research Laboratory (NRL)
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Overview and Objectives

❖ Task Description

✓ Deposit high performance optical broadband (FUV -> IR) mirror coatings:
  ✓ Fluorination/passivation of Al-based coatings.
  ✓ Atomic Layer Deposition (ALD) layers of AlF₃.
  ✓ Ion assisted depositions for low-absorption metal-fluoride to protect Al mirrors.

❖ Driver / Need

✓ Broadband coatings (90-10,000 nm) have been identified as an “Essential Goal” in the technology needs for a future Large-Aperture Ultraviolet-Optical-Infrared Space Telescope (LUVOIR and HabEx).

❖ Benefits

✓ High throughput & high signal-to-noise ratio (SNR) over a broad spectral range.
✓ Enabling technology for astrophysics and optical exoplanet sciences (in shared platform).
Hybrid PVD Passivation/Fluorination Chamber

Reactive fluorine compound with low bond energy used (e.g. XeF₂ with 133.9 kJ/Mole).

Heating of the XeF₂ may also be used if compound is not sufficiently reactive for increased selectivity.

XeF₂ is a dry-vacuum based method of reaction and requires no plasma or other activation minimizing damage to substrate.

Research Coating Chamber Upgrades

UHV Research Chamber capable of thin film physical vapor deposition (PVD) and passivation.

XeF$_2$ Gas feed components capable of continuous flow or pulsed flow.

Inside view of RC with 2-materia PVD deposition system.

R&D for combined PVD & fluorination of Al-based high performance FUV coatings.

Chamber is ready to be used and experimentation will start in 1-2 weeks (when FIREBALL primary mirror re-coating is done).
ALD Precursors For AlF₃ Depositions

Investigation of TMA and TiF₄ precursor systems:

Trimethyl aluminum (TMA) - Aluminum source
• Has been studied extensively for ALD use.
• Good vapor pressure.

Titanium tetrafluoride (TiF₄) - Fluoride source
• Has several cases of use in ALD; not as well-established.
• Requires heating to generate vapor pressure.
• Moderately acidic fluoride (as opposed to HF).
  Does not require additional activation (e-gun/plasma).

General-purpose ALD reactor features:
- The ALD process utilizes solid state halide precursors (TiF₄ and Trimethyl Aluminum (TMA) for the deposition of AlF₃ films.
- Solid state precursors precursor manifold plumbed for Ar, TMA, water, DEZn' room for 3 additional precursors.
- Optical access ports for real-time ellipsometry.
- Exhaust gate valve for "exposure" -mode operation.
- Accepts up to 2 inch substrates.
- Residual Gas Analyzer.

Simplified ALD Reactor Schematic Design

ALD Reactor at UMD
AlF₃ ALD Growth

- Extensive metrology to determine film composition, thickness & refractive index.
- Reduction of particle growth and “streaks by heating the Ar gas during purge.
- Earlier deposition runs resulted in films that were thinner than desired; a refill of the TiF₄ precursor and increased sublimate temperature resulted in substantially higher growth-per-ALD cycle.

Measured refractive index vs. film thickness for initial ALD runs on Si wafer: Red/blue - Max/min value measured on wafer.

Measured refractive index vs. film thickness with significant TiF₄ exposure on Si wafer: Red/blue - Max/min value measured on wafer.

UMD graduate student (Alan Uy) who is conducting ALD growth of AlF₃ as part of Ph.D. thesis.
Ti and O Impurities

TiO$_2$ Particle generation on Film

<table>
<thead>
<tr>
<th>Element</th>
<th>At % XPS</th>
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<tbody>
<tr>
<td>Al</td>
<td>22</td>
</tr>
<tr>
<td>F</td>
<td>68</td>
</tr>
<tr>
<td>O</td>
<td>6</td>
</tr>
<tr>
<td>Ti</td>
<td>2.2 (40% as TiO$_2$)</td>
</tr>
<tr>
<td>C</td>
<td>1.5</td>
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</tbody>
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TiF$_4$(a) more reactive to H$_2$O than O$_2$, but only at high $T$

$\rightarrow$ may occur when hot wafer is removed from reactor

$3\text{TiF}_4(g) + 2\text{A}_2\text{O}_3 \rightarrow 4\text{AlF}_3 + 3\text{TiO}_2$

$\rightarrow$ may be a route segment to TiO$_2$ contamination
ALD Reactor Re-design

- Improve across-wafer thickness and composition uniformity by eliminating reactor flow asymmetries.
- Reduce film impurities by simplifying the reactor design to eliminate potential leaks.
- Improve reactor wall and precursor delivery system heating to assure the lack of particles and to reduce potential contamination sources.
- Consideration of a load-lock to keep as much O₂ and water out of the reactor chamber.
Deposition of a ion-assisted physical vapor deposition (IAPVD) of FUV-optimized Al+metal fluoride overcoats (LiF, MgF2, and Al+AlF3) in the large 2-meter coating chamber.

- Acquisition of Ion Gun, optical monitor, deposition controller and PVD power supplies upgraded.
- Study of ZERODUR substrate to evaluate effect of heating on surface figure & wave-front error to demonstrate process on substrates traceable to a future telescope.
Ion-Assisted Coating Deposition

Procurement & installation of electron-gun for ion-assisted deposition to create more densely packed metal-fluoride coatings.

- Hollow Cathode (for operation without a filament).
- Deposition systems with critical dimensions greater than 1 meter.
- Favorable film properties in packing density, stress, environmental stability and stoichiometry.
- Process Gases:  Ar, Xe, Kr, O2, N2, Organic Precursors.
- Process: Pre-Cleaning, Surface Modification, Ion Beam Assisted Deposition, Direct Deposition.

View of Ion gun in operation inside 2-meter Chamber.
- Procurement & installation of an in-situ optical monitor ($\lambda = 121.6$ nm); source, detector, port window, etc.
- System will produce a collimated beam that will manage to deliver the collected light to a 10mm spot over a meter away. It uses a ISO NW40KF flanges for mounting and beam path.
Optimization Al+LiF (eLiF) Hot Coatings

The SISTINE primary mirror after coating with Al+LiF in 2-meter chamber at GSFC.
FIREBALL-2 Primary Mirror Re-coating

FIREBALL: Faint Intergalactic Redshifted Emission Balloon
- Balloon-borne 1m telescope coupled to an ultraviolet fiber-fed spectrograph.
- Designed to study the faint and diffuse emission of the intergalactic medium.
- Primary mirror is at GSFC going through re-polishing and re-coating with Al+MgF₂ in preparation for launch in 2020.
Al PVD Power Supply Reconfiguration

- Original power supply (5V, 3000 Amp) for Al deposition became unreliable.
- The Al deposition coils had to be reconfigured for a new power supply (30V, 500 Amp) in order to achieve the 100 A/Sec deposition rates.
- Setup up time is much longer in this new configuration (to avoid shorting leads for each Al coil.
- Long term plan is to buy and replace original power supply (estimated cost~ $48k).
Applications of ZERODUR

- ZERODUR® is a well-known mirror substrate material for ground and space based telescope application because of its low coefficient of thermal expansion ideal for ultra-stable optical systems.

- Coating of ZERODUR with enhance FUV coatings requires processing up to 250°C.

- Cooling ZERODUR® in the temperature range 130°C to 320°C with rates different from the typical production cooling rate of 3°C/h will change the CTE of the material with increasing temperature.¹

- Changes in CTE can sometimes lead to changes in surface figure.¹

Process

Pre-Treat Measurement

Zygo Interferometer

Heratherm Oven

Coatings Chamber

Post-Treat Measurement

MX Software
ZERODUR Heat Cycling

- Initial treatment is ramp down at 10 C/hr.
- Almost no difference observed in comparing CRA.
- Largest aberration change is Oblique Astigmatism (2 nm).

Collaborations:
Gabe Richardson (GSFC Pathways undergraduate, BYU)
Dave Sheikh (ZeCoat Corporation)

The injection of a 2 keV beam into the background gas will directly ionize and dissociate the gas.

- Beam energy well above ionization threshold.
- Higher beam energy = more efficient ionization.
Operating Parameters

- Gas manifold: Ar, SF₆, NH₃
- Flow rates: Ar (150 sccm); Molecular gases (0.5 sccm, SF₆ and 2.5 sccm NH₃)
- Pressure: 75 mTorr
- Process Time 240 s
- Beam Energy 2.5 keV, Cathode Current 20 mA
FUV Reflectance: Latest LAPPS Results

FUV Reflectance of E-beam + Radical Source Treatments of bare Al samples:

• Transition the low-temperature plasma fluorination process to a new reactor at NRL to provide a much cleaner chamber.
• Reflectance for a sample treated in this reactor 70% at 110 nm (O content ~ 6.5%).
• Reflectance is compared to data in Hennessy et.al.²
• Results show promising potential for passivation of fresh Al coatings mirrors in research chamber.


Path Forward

- **One-year no-cost extension in FY20:**
  - Perform XeF₂ passivation in Research Chamber.
  - Extensive re-design ALD reactor at UMD.
  - Conduct ion-assisted deposition in large (e.g. 2-meter chamber) to produce denser/lower absorption metal-fluoride films.
Conclusions

- Completed upgrades to a small (1-meter) research chamber for fluorination ($\text{XeF}_2$) of unoxidized Al mirrors.
- Ongoing progress in the ALD growth of $\text{AlF}_3$ with solid state precursors ($\text{TiF}_4$ and TMA).
- Complete procurement & installation of ion-gun and optical monitor for IAPVD depositions of metal-fluoride overcoats in GSFC 2-meter chamber.
- The LAPPS reactor (developed at NRL) has shown potential for oxide-removal & passivation of Al mirror.
- Initial trial runs of oxidized Al coatings with NLR LAPPS reactor showed improved FUV reflectance with treatment with the LAPPS e-beam in combination with a radical (fluorine) source.
- Chemical analysis confirmed presence of F bonds on the surfaces of Al samples (with reduced concentration of O) that correlated with improved FUV reflectance.
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